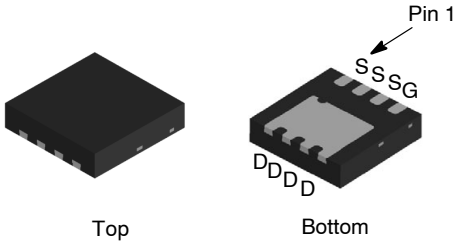
MOSFET – N-Channel, POWERTRENCH®

80 V, 22 A, 11.7 mΩ

FDMC86320



WDFN8 3.3x3.3, 0.65P
CASE 511DH

General Description

This N−Channel MOSFET has been designed specifically to improve the overall efficiency and to minimize switch node ringing of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{DS(on)}$, fast switching speed and body diode reverse recovery performance.

Features

- Max $r_{DS(on)}$ = 11.7 mΩ at V_{GS} = 10 V, I_D = 10.7 A
- Max $r_{DS(on)}$ = 16 mΩ at V_{GS} = 8 V, I_D = 8.5 A
- MSL1 Robust Package Design
- 100% UIL Tested
- These Devices are Pb−Free, Halide Free and are RoHS Compliant

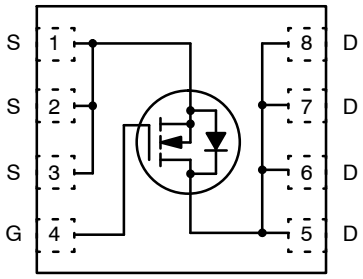
Applications

- Primary DC−DC Switch
- Motor Bridge Switch
- Synchronous Rectifier

MARKING DIAGRAM

FDMC	= Specific Device Code
86320	= Specific Device Code
&Z	= Assembly Location
&K	= Lot Run Traceability Code
&2	= Date Code (Year and Week)

PIN ASSIGNMENT



N−Channel MOSFET

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

MOSFET MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	80	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current −Continuous T_C = 25°C −Continuous T_A = 25°C (Note 1a) −Pulsed	 22 10.7 50	A
E_{AS}	Single Pulse Avalanche Energy (Note 3)	60	mJ
P_D	Power Dissipation T_C = 25°C	40	W
	Power Dissipation T_A = 25°C (Note 1a)	2.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

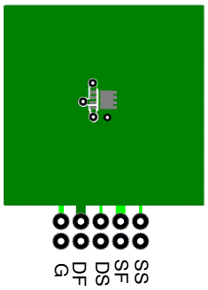
Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 1)	3.1	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

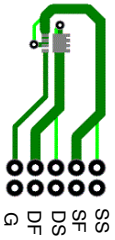
Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	80			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C		56		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 48 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2.4	3.5	4.5	V
$\Delta V_{GS(th)}/\Delta T_J$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C		−11		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 10.7 A		9.7	11.7	mΩ
		V_{GS} = 8 V, I_D = 8.5 A		11.4	16	
		V_{GS} = 10 V, I_D = 10.7 A, T_J = 125°C		15	18	
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 10.7 A		20		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 40 V, V_{GS} = 0 V, f = 1 MHz		1985	2640	pF
C_{oss}	Output Capacitance			353	469	pF
C_{rss}	Reverse Transfer Capacitance			12	30	pF
R_g	Gate Resistance			0.5		Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn−On Delay Time	V_{DD} = 40 V, I_D = 10.7 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		15	28	ns
t_r	Rise Time			8	16	ns
$t_{d(off)}$	Turn−Off Delay Time			20	35	ns
t_f	Fall Time			5	10	ns
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 40 V, I_D = 10.7 A		29	41	nC
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 8 V; V_{DD} = 40 V, I_D = 10.7 A		24	34	nC
Q_{gs}	Gate to Source Charge	V_{DD} = 40 V, I_D = 10.7 A		10		nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 40 V, I_D = 10.7 A		6.9		nC
DRAIN−SOURCE DIODE CHARACTERISTICS						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 10.7 A (Note 2)		0.84	1.3	V
		V_{GS} = 0 V, I_S = 2 A (Note 2)		0.75	1.2	
t_{rr}	Reverse Recovery Time	I_F = 10.7 A, di/dt = 100 A/μs		38	61	ns
Q_{rr}	Reverse Recovery Charge	I_F = 10.7 A, di/dt = 100 A/μs		27	43	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR−4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user’s board design.



a. 53 °C/W when mounted on a 1 in^2 pad of 2 oz copper.



b. 125 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0 %.
3. Starting T_J = 25 °C, N−ch: L = 0.3 mH, I_{AS} = 20 A, V_{DD} = 72 V, V_{GS} = 10 V.

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

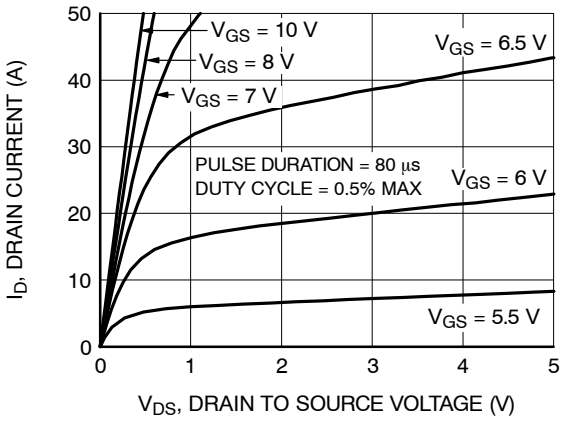


Figure 1. On−Region Characteristics

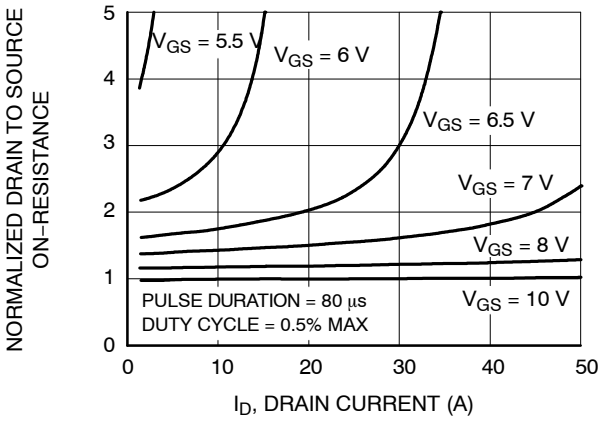


Figure 2. Normalized On−Resistance vs. Drain Current and Gate Voltage

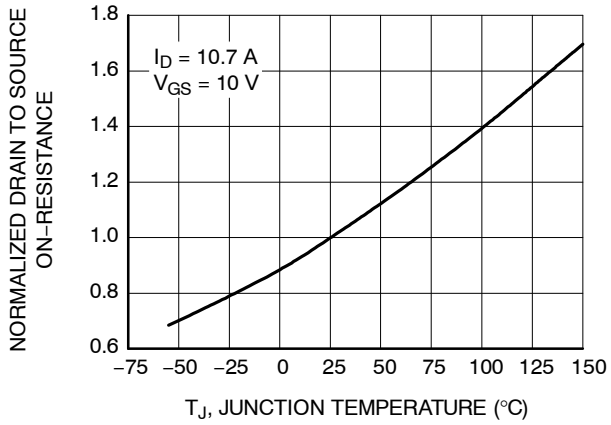


Figure 3. Normalized On−Resistance vs. Junction Temperature

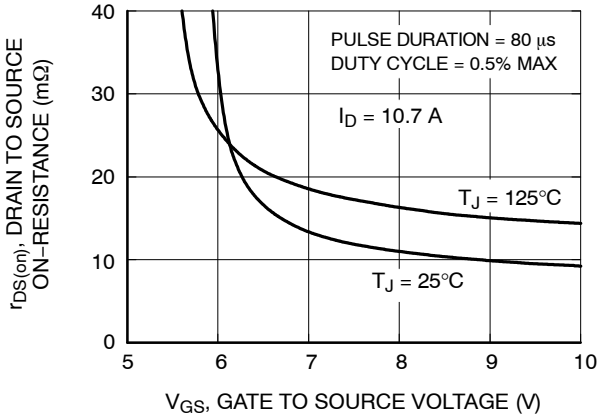


Figure 4. On−Resistance vs. Gate to Source Voltage

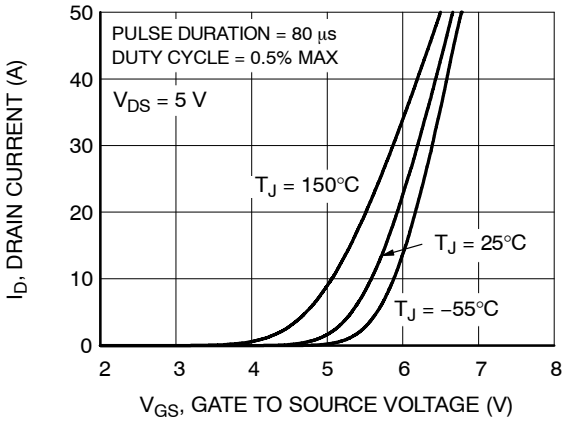


Figure 5. Transfer Characteristics

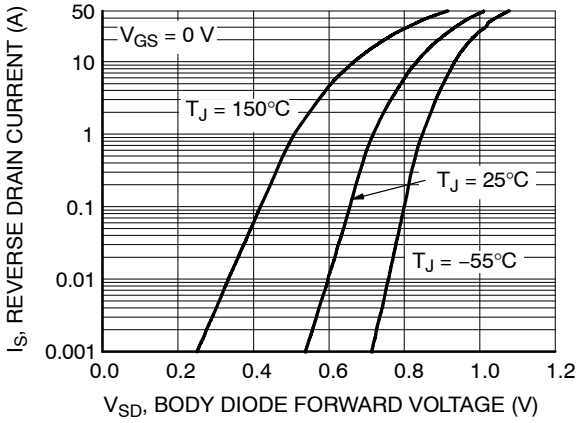


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (continued)

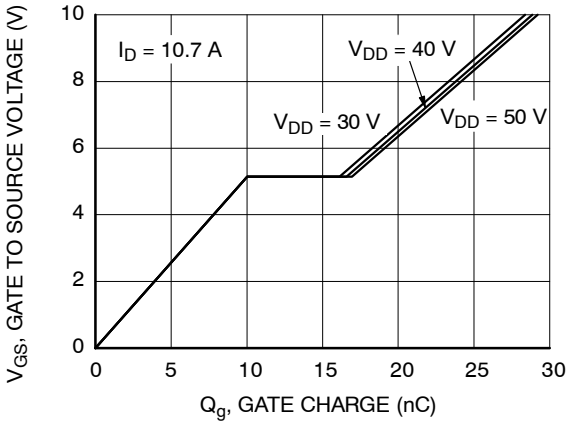


Figure 7. Gate Charge Characteristics

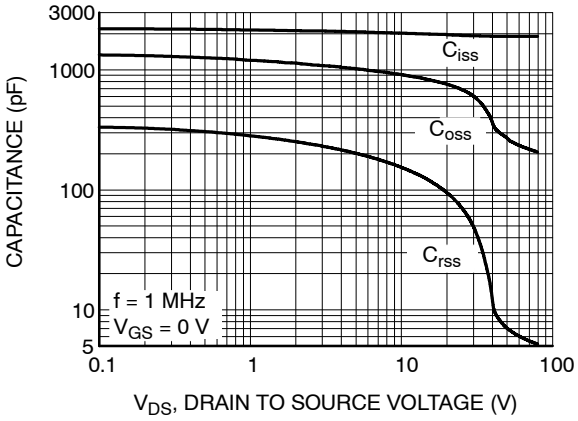


Figure 8. Capacitance vs. Drain to Source Voltage

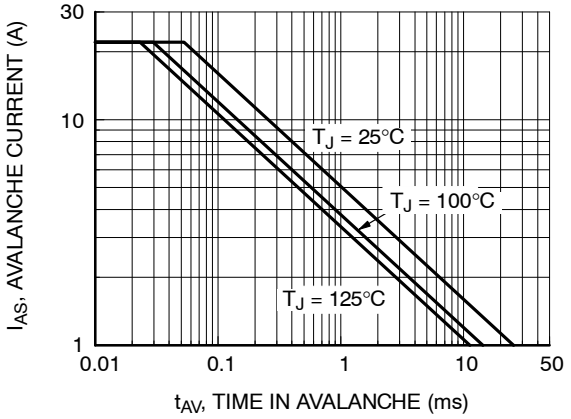


Figure 9. Unclamped Inductive Switching Capability

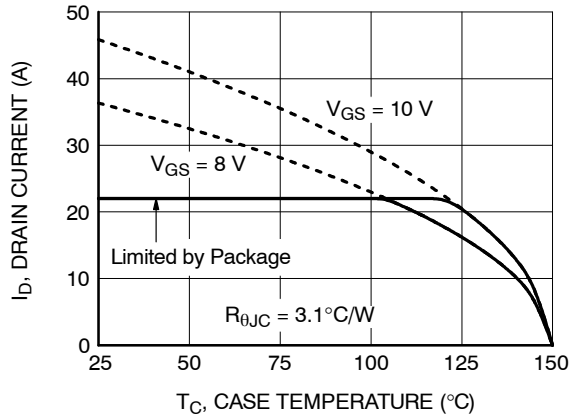


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

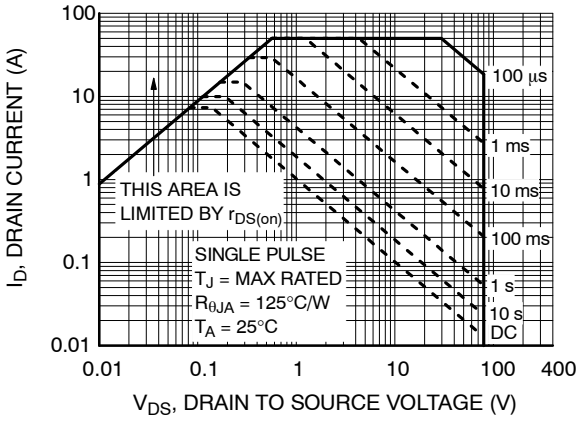


Figure 11. Forward Bias Safe Operating Area

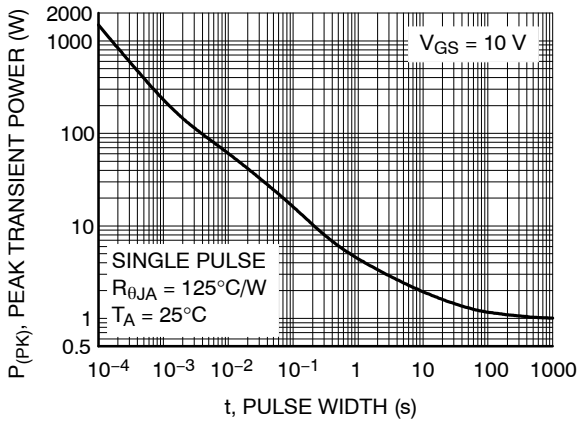


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (continued)

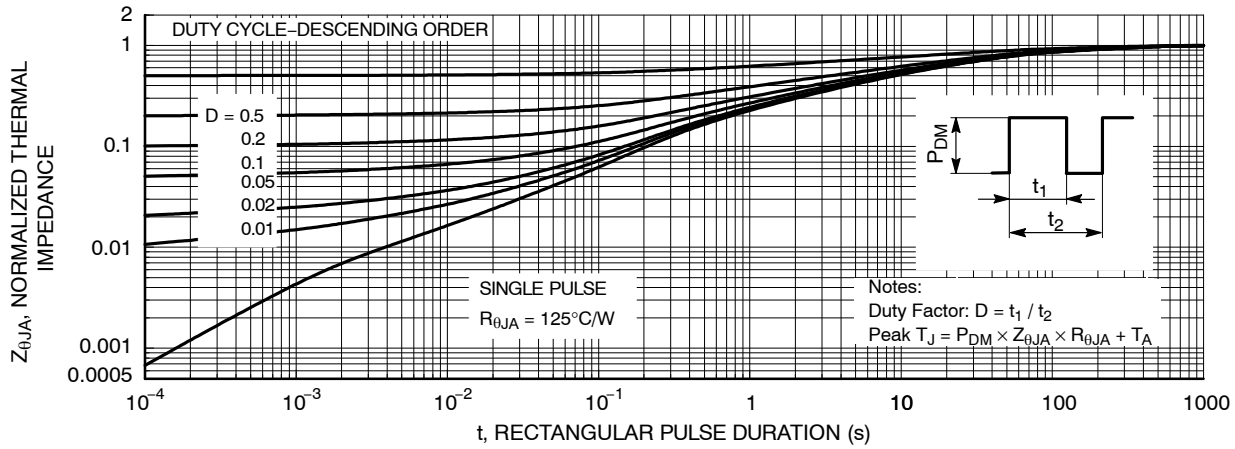


Figure 13. Junction−to−Case Transient Thermal Response Curve

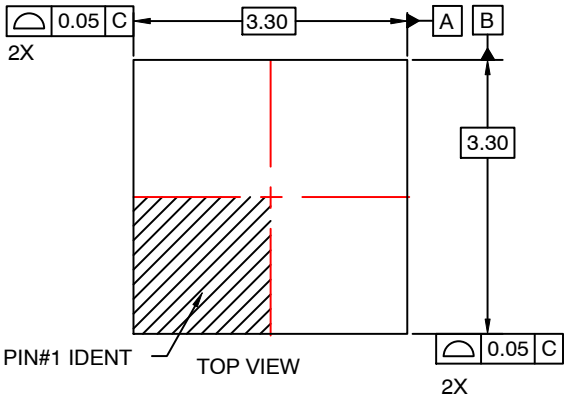
ORDERING INFORMATION

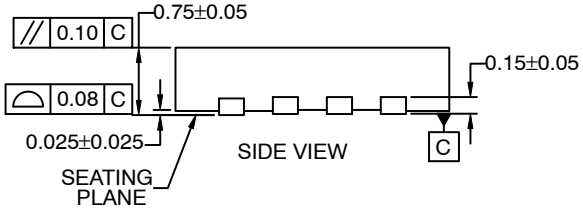
Device	Device Marking	Package Type	Shipping†
FDMC86320	FDMC86320	WDFN8 3.3x3.3, 0.65P (Pb−Free)	3000 / Tape & Reel

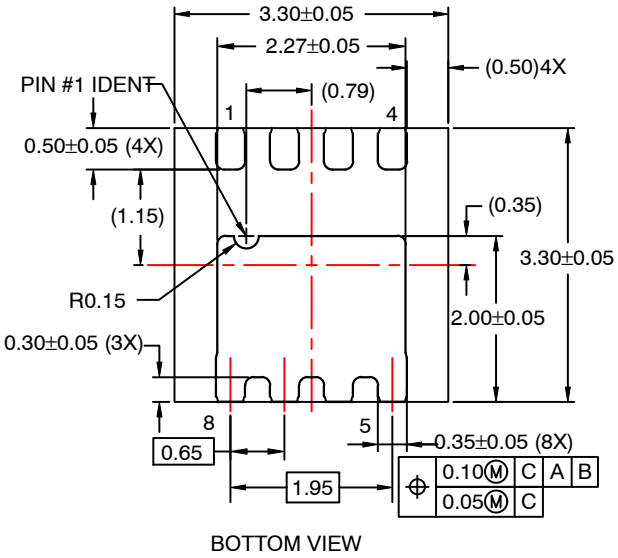
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

WDFN8 3.3x3.3, 0.65P
CASE 511DH
ISSUE O

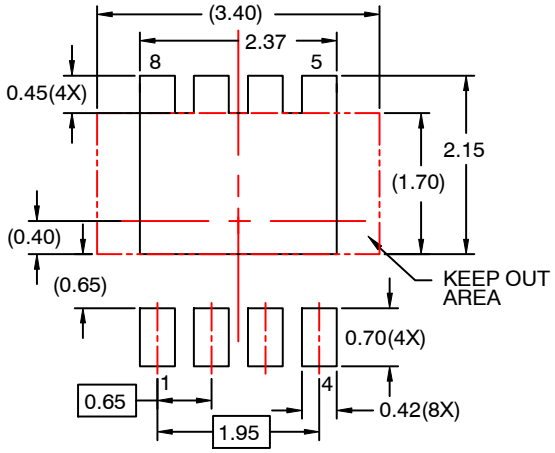
DATE 31 JUL 2016







BOTTOM VIEW



RECOMMENDED LAND PATTERN

NOTES:

A. DOES NOT CONFORM TO JEDEC REGISTRATION MO−229

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.

D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

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DESCRIPTION:	**WDFN8 3.3X3.3, 0.65P**	**PAGE 1 OF 1**

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